Material Composition Declaration

EPC2378

Company Name	Efficient Power Conversion (EPC)	Issue Date:	06/08/2026
Contact Name:	Yanping Ma	Contact Title:	VP Quality
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Part Weight:	26.0 mg	Type of Product:	eGaN FET in FCQFN package

Construction Element	Substance	CAS No. If Applicable	Weight (mg)	Mass (%)	Sum (%)	Mass (ppm)
Chip	Silicon	7440-21-3	6.3740	24.5497	25.6308	245497
	Silicon oxide	7631-86-9	0.0301	0.1159		1159
	Silicon nitride	12033-89-5	0.0254	0.0978		978
	Gallium nitride	25617-97-4	0.0352	0.1357		1357
	Aluminum	7429-90-5	0.0830	0.3199		3199
	Aluminum nitride	24304-00-5	0.0060	0.0231		231
	Titanium	7440-32-6	0.0013	0.0052		52
	Titanium nitride	25583-20-4	0.0058	0.0223		223
	Copper	7440-50-8	0.0014	0.0053		53
	Tungsten	7440-33-7	0.0105	0.0403		403
	Polyimide		0.0820	0.3157		3157
Under Bump Metal	Titanium	7440-32-6	0.0011	0.0041	0.0451	41
	Copper	7440-50-8	0.0106	0.0410		410
Internal Solder Bump	Copper	7440-50-8	1.3188	5.0794	6.6510	50794
	Nickel	7440-02-0	0.0634	0.2443		2443
	Tin	7440-31-5	0.3384	1.3034		13034
	Silver	7440-22-4	0.0062	0.0239		239
Package	Copper	7440-50-8	11.8921	45.8027	66.8874	458027
	Mold Compound		5.4744	21.0847		210847
External pins Coating	Nickel	7440-02-0	0.2006	0.7728	0.7858	7728
	Palladium	7440-05-3	0.0018	0.0071		71
	Potassium Gold Cyanide	13967-50-5	0.0015	0.0059		59
Sum in total:			25.96	100.00	100.00	1000000

Note:

The substance content disclosed herewith is approximate and is based on engineering calculation. Statements are based on our present knowledge and may subject to change at any time due to technical requirements and development. EPC may update this document without notification. Statement may not include information regarding the minute quantities of dopant and metal materials in the electrical devices contained within the finished product.